64M-BIT MASK-PROGRAMMABLE ROM
8M-WORD BY 8-BIT (BYTE MODE) / 4M-WORD BY 16-BIT (WORD MODE)
PAGE ACCESS MODE

Description

The μPD23C64040JL, 23C64080JL are a 67,108,864 bits mask-programmable ROM. The word organization is selectable (BYTE mode : 8,388,608 words by 8 bits, WORD mode : 4,194,304 words by 16 bits).

The active levels of OE (Output Enable Input) can be selected with mask-option.

The μPD23C64040JL, 23C64080JL are packed in 48-pin PLASTIC TSOP (I) and 44-pin PLASTIC SOP.

Features

• Word organization

  8,388,608 words by 8 bits (BYTE mode)

  4,194,304 words by 16 bits (WORD mode)

• Page access mode

  BYTE mode : 8 byte random page access (μPD23C64040JL)

             : 16 byte random page access (μPD23C64080JL)

  WORD mode : 4 word random page access (μPD23C64040JL)

             : 8 word random page access (μPD23C64080JL)

• Operating supply voltage : V_{CC} = 2.7 to 3.6 V

Operating supply voltage V_{CC}	Package	Access time / Page access time ns (MAX.)	Power supply current (Active mode) mA (MAX.)		Standby current (CMOS level input) μA (MAX.)
			μPD23C64040JL	μPD23C64080JL	
3.0 V ± 0.3 V	TSOP (I)	100 / 25	40	60	30
	SOP	120 / 25	35	50	
3.3 V ± 0.3 V	TSOP (I)	90 / 25	55	75	
	SOP	100 / 25	50	65	

Remark The access time and power supply current vary depending on the package type.

The mark ★ shows major revised points.

© NEC Electronics Corporation 2002

Ordering Information

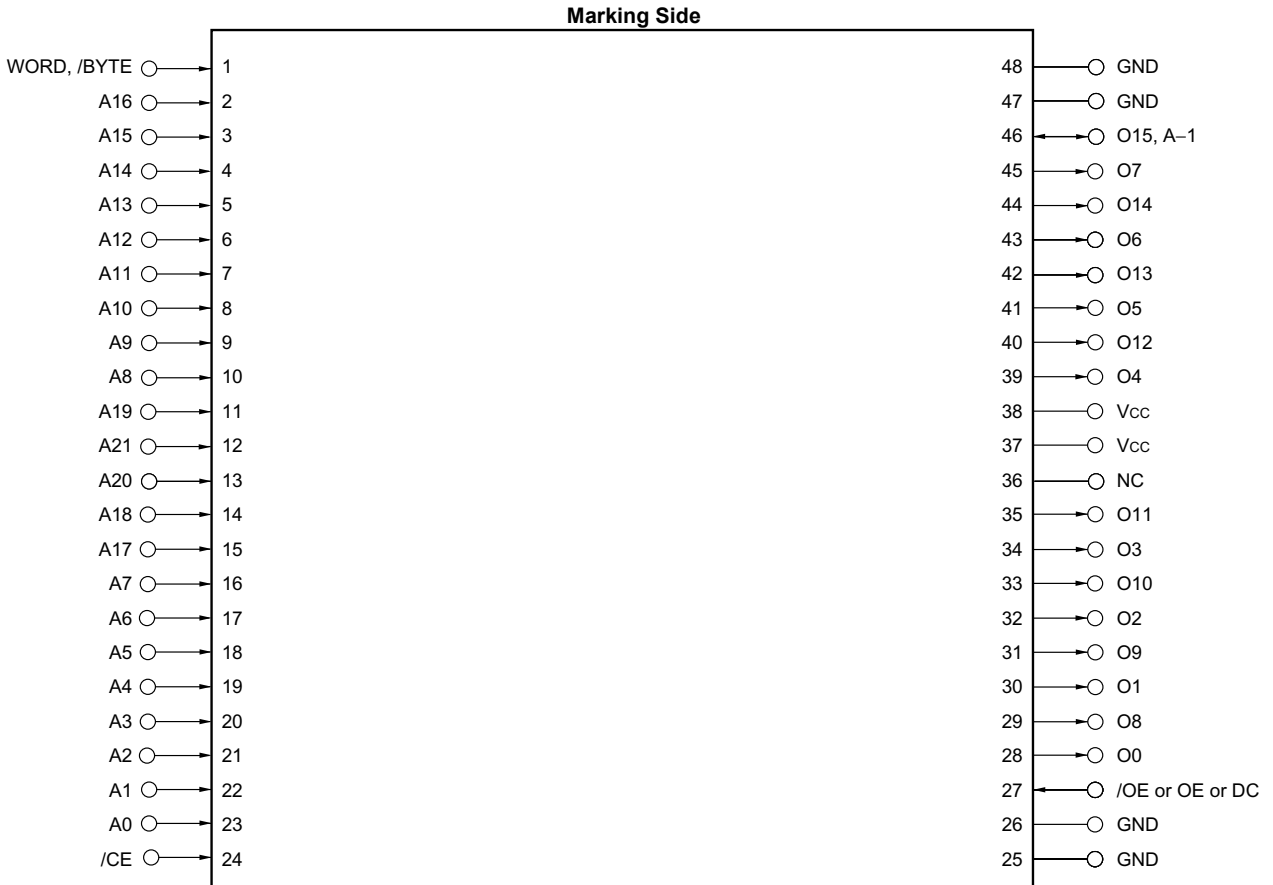| Part number	Package
μPD23C64040JLGY-xxx-MJH	48-pin PLASTIC TSOP (I) (12 $\times$ 18) (Normal bent)
μPD23C64040JLGY-xxx-MKH	48-pin PLASTIC TSOP (I) (12 $\times$ 18) (Reverse bent)
μPD23C64040JLGX-xxx	44-pin PLASTIC SOP (15.24 mm (600))
μPD23C64080JLGY-xxx-MJH	48-pin PLASTIC TSOP (I) (12 $\times$ 18) (Normal bent)
μPD23C64080JLGY-xxx-MKH	48-pin PLASTIC TSOP (I) (12 $\times$ 18) (Reverse bent)
μPD23C64080JLGX-xxx	44-pin PLASTIC SOP (15.24 mm (600))

(xxx : ROM code suffix No.)

Pin Configurations

/xxx indicates active low signal.

48-pin PLASTIC TSOP (I) (12 × 18) (Normal bent)
[μPD23C64040JLGY-xxx-MJH]
[μPD23C64080JLGY-xxx-MJH]

Marking Side

Left Pin	No.		No.	Right Pin
WORD, /BYTE	1		48	GND
A16	2		47	GND
A15	3		46	O15, A−1
A14	4		45	O7
A13	5		44	O14
A12	6		43	O6
A11	7		42	O13
A10	8		41	O5
A9	9		40	O12
A8	10		39	O4
A19	11		38	Vcc
A21	12		37	Vcc
A20	13		36	NC
A18	14		35	O11
A17	15		34	O3
A7	16		33	O10
A6	17		32	O2
A5	18		31	O9
A4	19		30	O1
A3	20		29	O8
A2	21		28	O0
A1	22		27	/OE or OE or DC
A0	23		26	GND
/CE	24		25	GND

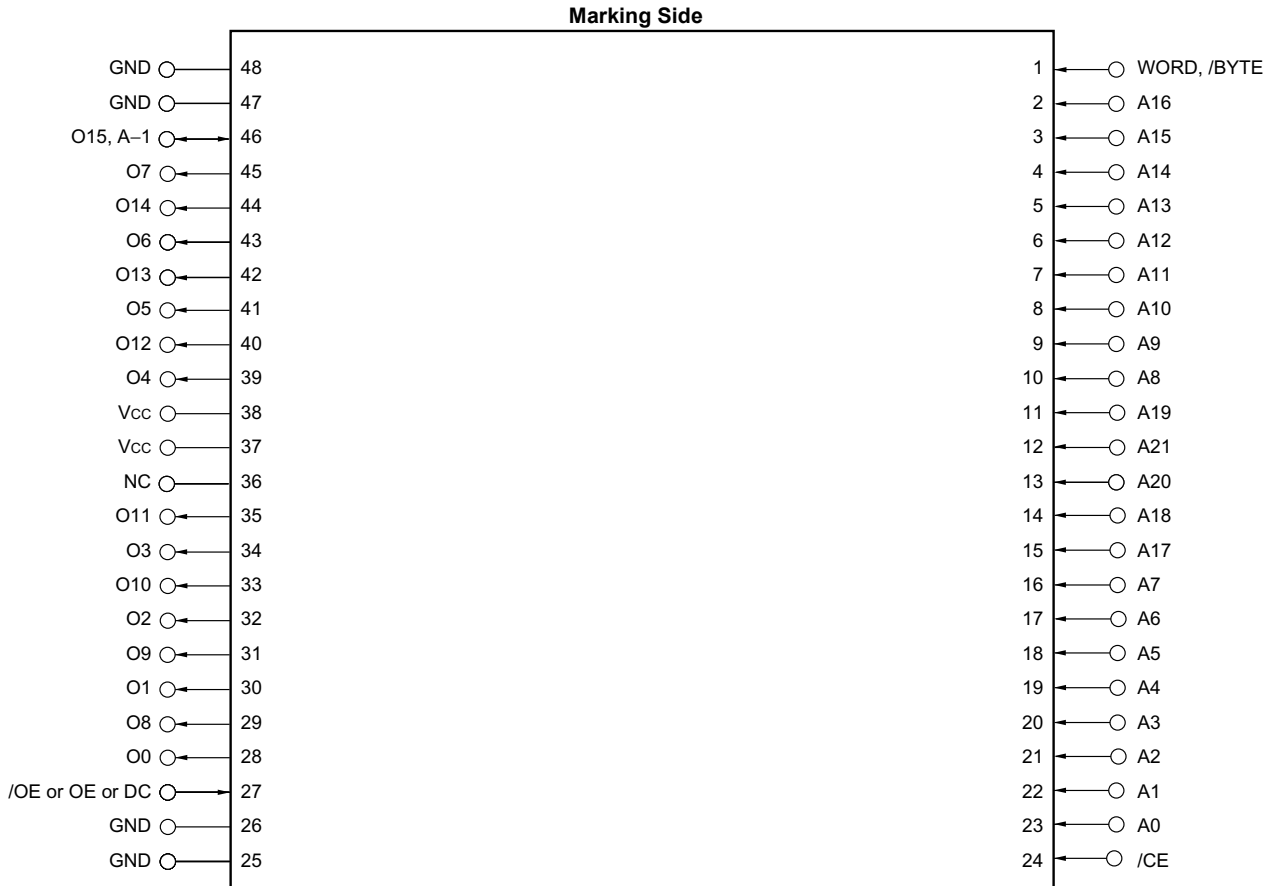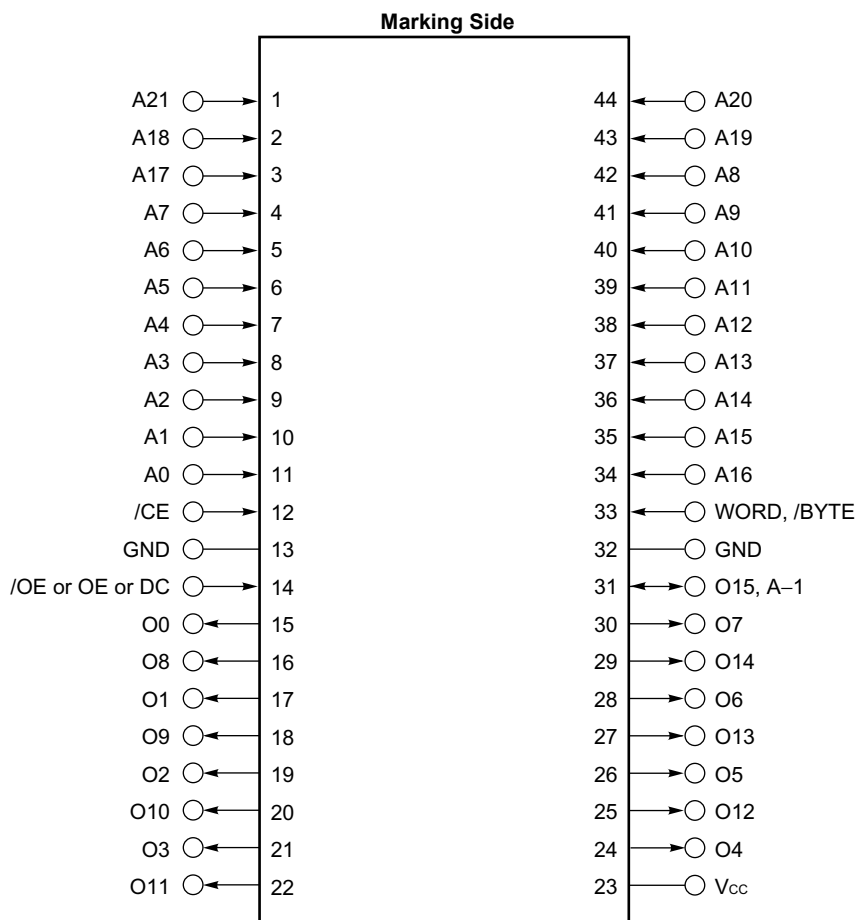| Signal	Description
A0 to A21	: Address inputs
O0 to O7, O8 to O14	: Data outputs
O15, A−1	: Data output 15 (WORD mode), LSB Address input (BYTE mode)
WORD, /BYTE	: Mode select input
/CE	: Chip Enable input
/OE or OE	: Output Enable input
Vcc	: Supply voltage
GND	: Ground
NC [Note]	: No Connection
DC	: Don't Care

Note Some signals can be applied because this pin is not connected to the inside of the chip.

Remark Refer to **Package Drawings** for the 1-pin index mark.

48-pin PLASTIC TSOP (I) (12 × 18) (Reverse bent)
[μPD23C64040JLGY-xxx-MKH]
[μPD23C64080JLGY-xxx-MKH]

Marking Side

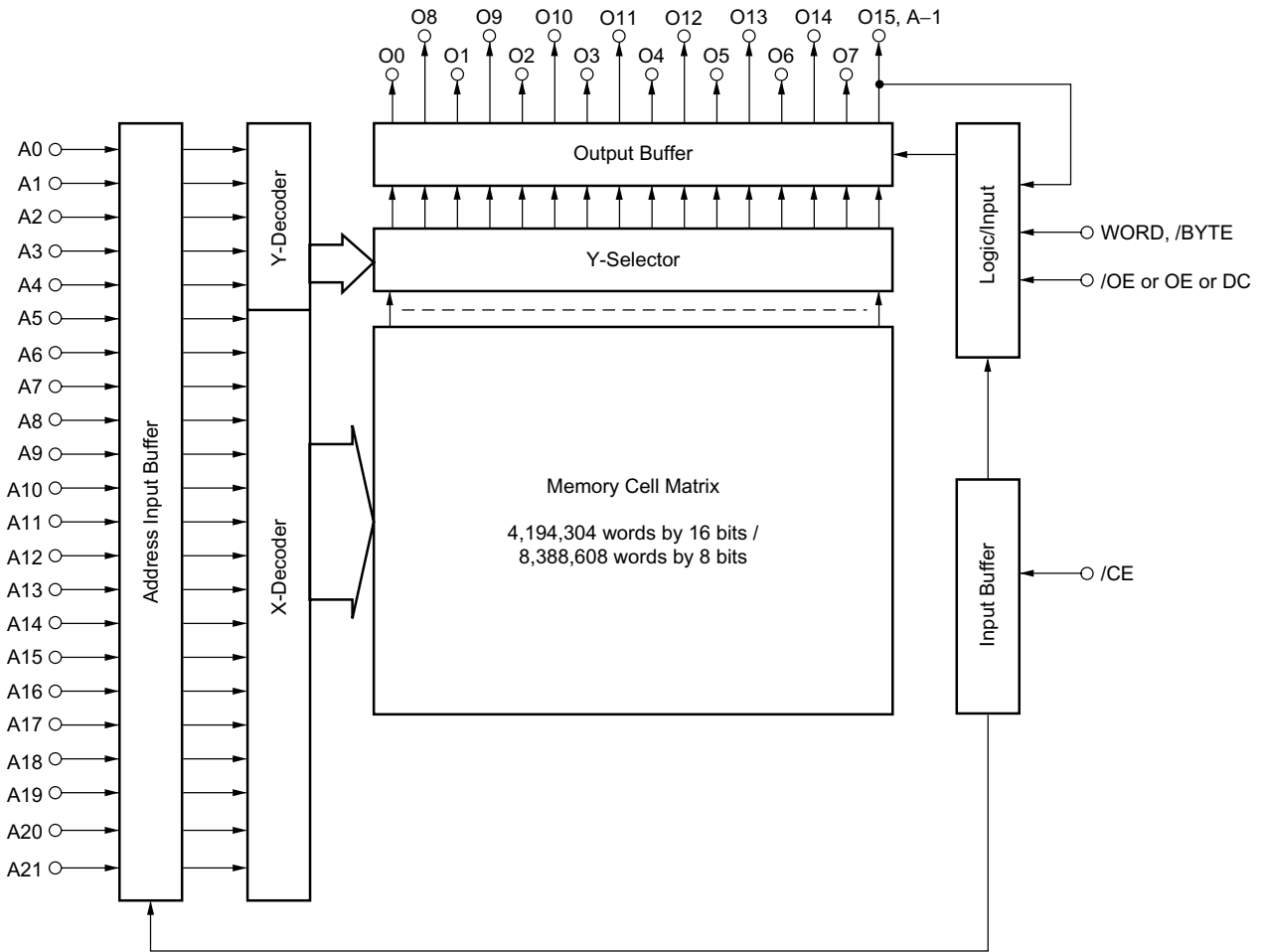| Left pin	Pin #		Pin #	Right pin
GND	48		1	WORD, /BYTE
GND	47		2	A16
O15, A−1	46		3	A15
O7	45		4	A14
O14	44		5	A13
O6	43		6	A12
O13	42		7	A11
O5	41		8	A10
O12	40		9	A9
O4	39		10	A8
Vcc	38		11	A19
Vcc	37		12	A21
NC	36		13	A20
O11	35		14	A18
O3	34		15	A17
O10	33		16	A7
O2	32		17	A6
O9	31		18	A5
O1	30		19	A4
O8	29		20	A3
O0	28		21	A2
/OE or OE or DC	27		22	A1
GND	26		23	A0
GND	25		24	/CE

A0 to A21	: Address inputs
O0 to O7, O8 to O14	: Data outputs
O15, A−1	: Data output 15 (WORD mode),
	LSB Address input (BYTE mode)
WORD, /BYTE	: Mode select input
/CE	: Chip Enable input
/OE or OE	: Output Enable input
Vcc	: Supply voltage
GND	: Ground
NC Note	: No Connection
DC	: Don't Care

Note Some signals can be applied because this pin is not connected to the inside of the chip.

Remark Refer to **Package Drawings** for the 1-pin index mark.

44-pin PLASTIC SOP (15.24 mm (600))

[μPD23C64040JLGX-xxx]

[μPD23C64080JLGX-xxx]

Marking Side

Left pin	Pin no.		Pin no.	Right pin
A21	1		44	A20
A18	2		43	A19
A17	3		42	A8
A7	4		41	A9
A6	5		40	A10
A5	6		39	A11
A4	7		38	A12
A3	8		37	A13
A2	9		36	A14
A1	10		35	A15
A0	11		34	A16
/CE	12		33	WORD, /BYTE
GND	13		32	GND
/OE or OE or DC	14		31	O15, A−1
O0	15		30	O7
O8	16		29	O14
O1	17		28	O6
O9	18		27	O13
O2	19		26	O5
O10	20		25	O12
O3	21		24	O4
O11	22		23	Vcc

A0 to A21	: Address inputs
O0 to O7, O8 to O14	: Data outputs
O15, A−1	: Data output 15 (WORD mode),
	LSB Address input (BYTE mode)
WORD, /BYTE	: Mode select input
/CE	: Chip Enable input
/OE or OE	: Output Enable input
Vcc	: Supply voltage
GND	: Ground
DC	: Don't Care

Remark   Refer to **Package Drawings** for the 1-pin index mark.

Input / Output Pin Functions

Pin name	Input / Output	Function
WORD, /BYTE	Input	The pin for switching WORD mode and BYTE mode. **High level** : WORD mode (4M-word by 16-bit) **Low level** : BYTE mode (8M-word by 8-bit)
A0 to A21 (Address inputs)	Input	Address input pins. A0 to A21 are used differently in the WORD mode and the BYTE mode. **WORD mode (4M-word by 16-bit)** A0 to A21 are used as 22 bits address signals. **BYTE mode (8M-word by 8-bit)** A0 to A21 are used as the upper 22 bits of total 23 bits of address signal. (The least significant bit (A$-$1) is combined to O15.)
O0 to O7, O8 to O14 (Data outputs)	Output	Data output pins. O0 to O7, O8 to O14 are used differently in the WORD mode and the BYTE mode. **WORD mode (4M-word by 16-bit)** The lower 15 bits of 16 bits data outputs to O0 to O14. (The most significant bit (O15) combined to A$-$1.) **BYTE mode (8M-word by 8-bit)** 8 bits data outputs to O0 to O7 and also O8 to O14 are high impedance.
O15, A$-$1 (Data output 15, LSB Address input)	Output, Input	O15, A$-$1 are used differently in the WORD mode and the BYTE mode. **WORD mode (4M-word by 16-bit)** The most significant output data bus (O15). **BYTE mode (8M-word by 8-bit)** The least significant address bus (A$-$1).
/CE (Chip Enable)	Input	Chip activating signal. When the OE is active, output states are following. **High level**: High-Z **Low level** : Data out
/OE or OE or DC (Output Enable, Don't Care)	Input	Output enable signal. The active level of OE is mask option. The active level of OE can be selected from high active, low active and Don't care at order.
V$_{CC}$	–	Supply voltage
GND	–	Ground
NC	–	Not internally connected (The signal can be connected).

Block Diagram

Mask Option

The active levels of output enable pin (/OE or OE or DC) are mask programmable and optional, and can be selected from among "0" "1" "$\times$" shown in the table below.

Option	/OE or OE or DC	OE active level
0	/OE	L
1	OE	H
$\times$	DC	Don't care

Operation modes for each option are shown in the tables below.

Operation mode (Option : 0)

/CE	/OE	Mode	Output state
L	L	Active	Data out
	H		High-Z
H	H or L	Standby	High-Z

Operation mode (Option : 1)

/CE	OE	Mode	Output state
L	L	Active	High-Z
	H		Data out
H	H or L	Standby	High-Z

Operation mode (Option : $\times$)

/CE	DC	Mode	Output state
L	H or L	Active	Data out
H	H or L	Standby	High-Z

Remark   L : Low level input

H : High level input

Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V_{CC}		–0.3 to +4.6	V
Input voltage	V_I		–0.3 to V_{CC} + 0.3	V
Output voltage	V_O		–0.3 to V_{CC} + 0.3	V
Operating ambient temperature	T_A		–10 to +70	°C
Storage temperature	T_{stg}		–65 to +150	°C

Caution   Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Capacitance (T_A = 25 °C)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	C_I	f = 1 MHz			10	pF
Output capacitance	C_O				12	pF

DC Characteristics (T_A = –10 to +70 °C, V_{CC} = 2.7 to 3.6 V)

Parameter	Symbol	Test condition			MIN.	TYP.	MAX.	Unit
High level input voltage	V_{IH}				2.0		V_{CC} + 0.3	V
Low level input voltage	V_{IL}	V_{CC} = 3.0 V ± 0.3 V			–0.3		+0.5	V
		V_{CC} = 3.3 V ± 0.3 V			–0.3		+0.8	
High level output voltage	V_{OH}	I_{OH} = –100 μA			2.4			V
Low level output voltage	V_{OL}	I_{OL} = 2.1 mA					0.4	V
Input leakage current	I_{LI}	V_I = 0 V to V_{CC}			–10		+10	μA
Output leakage current	I_{LO}	V_O = 0 V to V_{CC}, Chip deselected			–10		+10	μA
Power supply current	I_{CC1}	/CE = V_{IL} (Active mode), I_O = 0 mA	μPD23C64040JL					
			V_{CC} = 3.0 V ± 0.3 V	TSOP (I)			40	mA
				SOP			35	
			V_{CC} = 3.3 V ± 0.3 V	TSOP (I)			55	
				SOP			50	
			μPD23C64080JL					
			V_{CC} = 3.0 V ± 0.3 V	TSOP (I)			60	mA
				SOP			50	
			V_{CC} = 3.3 V ± 0.3 V	TSOP (I)			75	
				SOP			65	
Standby current	I_{CC3}	/CE = V_{CC} – 0.2 V (Standby mode)					30	μA

AC Characteristics (T$_A$ = –10 to +70 °C, V$_{CC}$ = 2.7 to 3.6 V)

Parameter	Symbol	Test condition	V$_{CC}$ = 3.0 V ± 0.3 V			V$_{CC}$ = 3.3 V ± 0.3 V			Unit
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Address access time	t$_{ACC}$	TSOP (I)			100			90	ns
		SOP			120			100	
Page access time	t$_{PAC}$				25			25	ns
★ Address skew time	t$_{SKEW}$	**Note**			10			10	ns
Chip enable access time	t$_{CE}$	TSOP (I)			100			90	ns
		SOP			120			100	
Output enable access time	t$_{OE}$				25			25	ns
Output hold time	t$_{OH}$		0			0			ns
Output disable time	t$_{DF}$		0		25	0		25	ns
WORD, /BYTE access time	t$_{WB}$	TSOP (I)			100			90	ns
		SOP			120			100	

★ **Note** t$_{SKEW}$ indicates the following three types of time depending on the condition.

　　1) When switching /CE from high level to low level, t$_{SKEW}$ is the time from the /CE low level input point until the next address is determined.

　　2) When switching /CE from low level to high level, t$_{SKEW}$ is the time from the address change start point to the /CE high level input point.

　　3) When /CE is fixed to low level, t$_{SKEW}$ is the time from the address change start point until the next address is determined.

　　Since specs are defined for t$_{SKEW}$ only when /CE is active, t$_{SKEW}$ is not subject to limitations when /CE is switched from high level to low level following address determination, or when the address is changed after /CE is switched from low level to high level.

Remark t$_{DF}$ is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.

AC Test Conditions

Input waveform (Rise / Fall Time ≤ 5 ns)

1.4 V ← Test points → 1.4 V

Output waveform

1.4 V ← Test points → 1.4 V
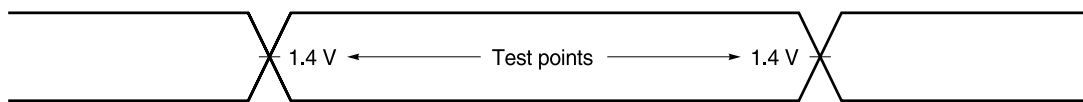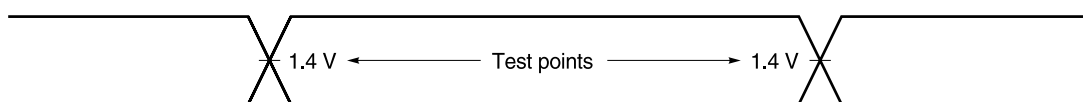
Output load

　　1 TTL + 100 pF

★ **Cautions on power application**

To ensure normal operation, always apply power using /CE following the procedure shown below.

1) Input a high level to /CE during and after power application.
2) Hold the high level input to /CE for 200 ns or longer (wait time).
3) Start normal operation after the wait time has elapsed.

Power Application Timing Chart 1 (When /CE is made high at power application)
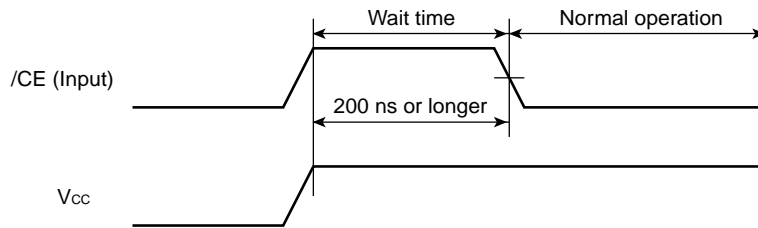
Power Application Timing Chart 2 (When /CE is made high after power application)
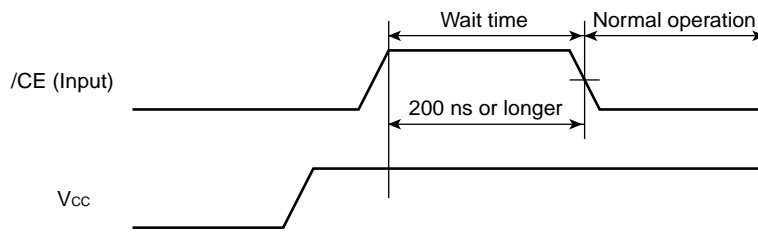
Caution Other signals can be either high or low during the wait time.

★ **Read Cycle Timing Chart 1**
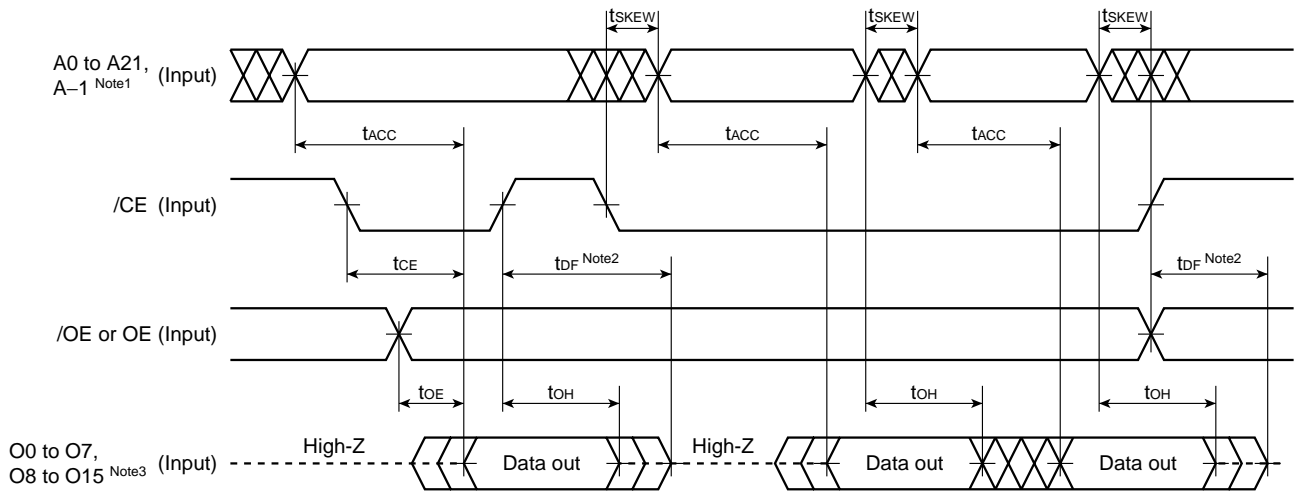
Notes 1. During WORD mode, A−1 is O15.

2. t_{DF} is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.

3. During BYTE mode, O8 to O14 are high impedance and O15 is A−1.

Read Cycle Timing Chart 2 (Page Access Mode)

Upper address[Note 1]
$\begin{bmatrix} A2 \text{ to } A21 \\ A3 \text{ to } A21 \end{bmatrix}$ (Input)

t_{ACC}

/CE (Input)

t_{CE}

/OE or OE (Input)

t_{OE}

Page address[Note 1]
$\begin{bmatrix} A-1^{[Note 2]}, A0, A1 \\ A-1^{[Note 2]}, A0, A1, A2 \end{bmatrix}$ (Input)

t_{PAC} [Note 5] t_{PAC} [Note 5] t_{DF} [Note 3]

t_{OH} t_{OH} t_{OH}

O0 to O7,
O8 to O15[Note 4] (Output)   High-Z   Data Out   Data Out   Data Out   High-Z
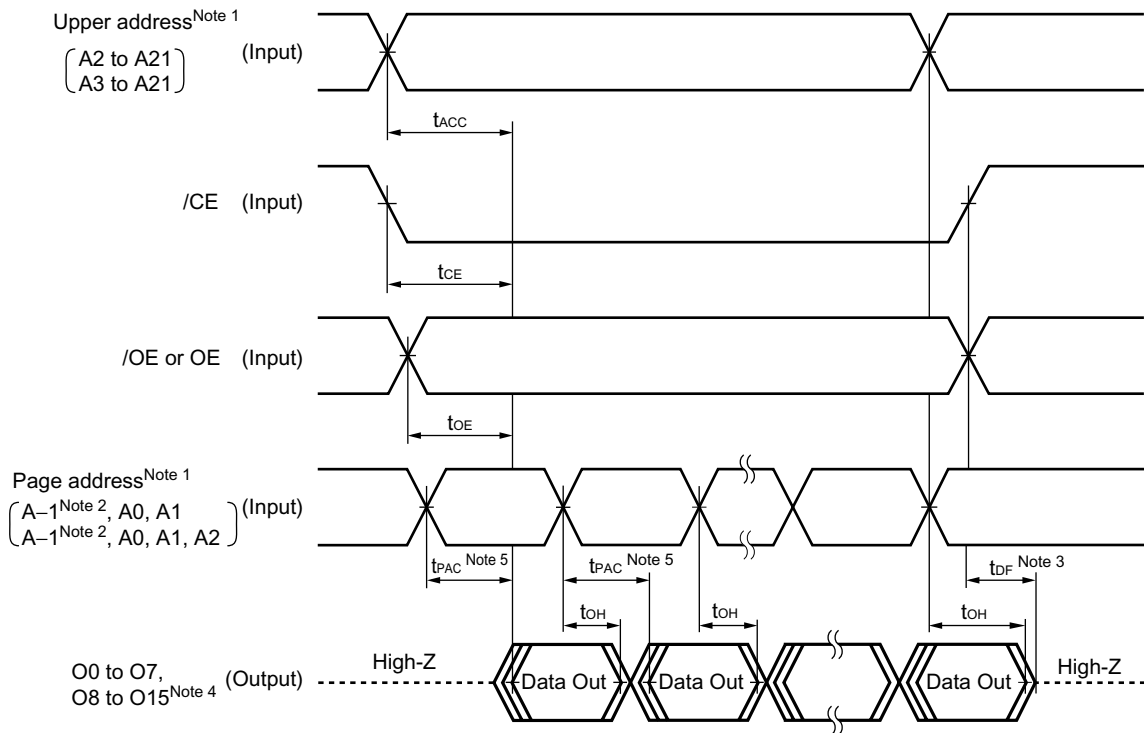
Notes 1. The address differs depending on the product as follows.

Part Number	Upper address	Page address
μPD23C64040JL	A2 to A21	A-1, A0, A1
μPD23C64080JL	A3 to A21	A-1, A0, A1, A2

2. During WORD mode, A-1 is O15.

3. t_{DF} is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.

4. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.

5. The definition of page access time is as follows.

[μPD23C64040JL]

Page access time	Upper address (A2 to A21) inputs condition	/CE input condition	/OE or OE input condition
t_{PAC}	Before $t_{ACC} - t_{PAC}$	Before $t_{CE} - t_{PAC}$	Before stabilizing of page address (A-1, A0, A1)

[μPD23C64080JL]

Page access time	Upper address (A3 to A21) inputs condition	/CE input condition	/OE or OE input condition
t_{PAC}	Before $t_{ACC} - t_{PAC}$	Before $t_{CE} - t_{PAC}$	Before stabilizing of page address (A-1, A0, A1, A2)

WORD, /BYTE Switch Timing Chart
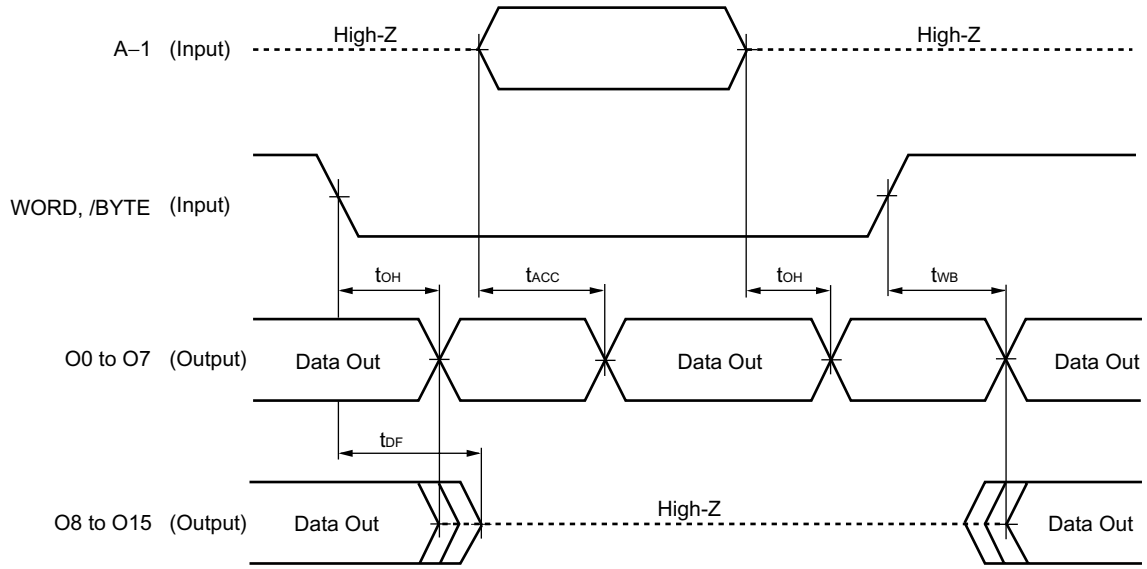
Remark Chip Enable (/CE) and Output Enable (/OE or OE) : Active.

Package Drawings

48-PIN PLASTIC TSOP(I) (12x18)
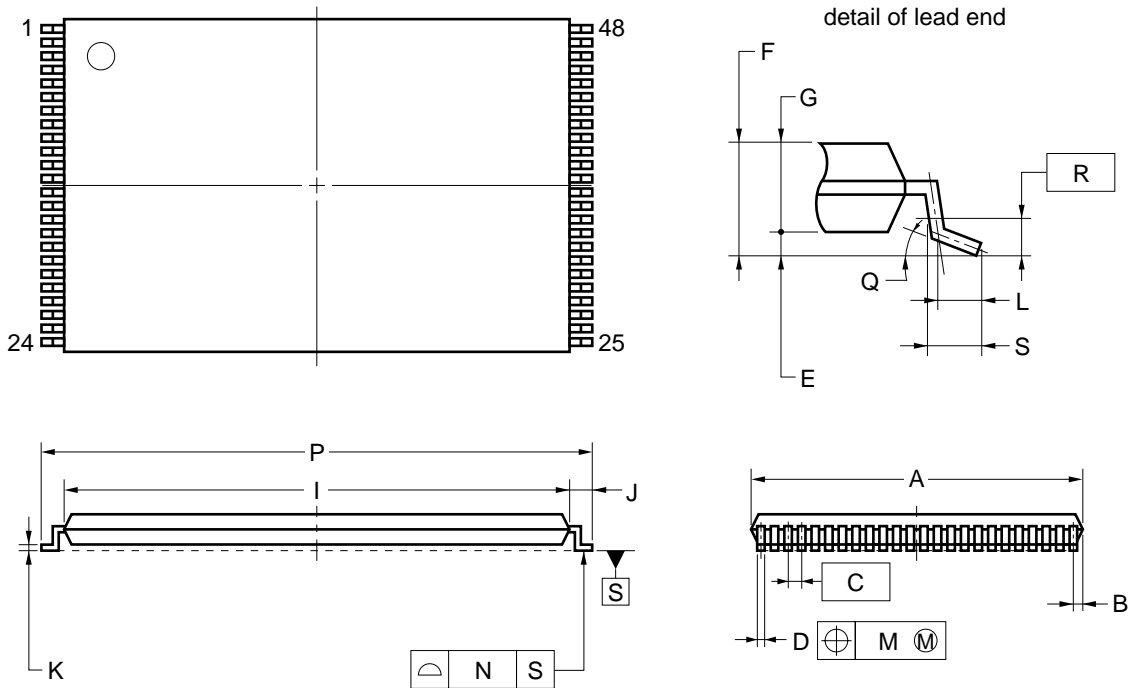
detail of lead end

NOTES

1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

2. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

ITEM	MILLIMETERS
A	12.0±0.1
B	0.45 MAX.
C	0.5 (T.P.)
D	0.22±0.05
E	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
I	16.4±0.1
J	0.8±0.2
K	0.145±0.05
L	0.5
M	0.10
N	0.10
P	18.0±0.2
Q	$3°^{+5°}_{-3°}$
R	0.25
S	0.60±0.15

S48GY-50-MJH1-1

48-PIN PLASTIC TSOP(I) (12x18)

detail of lead end

NOTES

1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

2. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

ITEM	MILLIMETERS
A	12.0±0.1
B	0.45 MAX.
C	0.5 (T.P.)
D	0.22±0.05
E	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
I	16.4±0.1
J	0.8±0.2
K	0.145±0.05
L	0.5
M	0.10
N	0.10
P	18.0±0.2
Q	$3°^{+5°}_{-3°}$
R	0.25
S	0.60±0.15

S48GY-50-MKH1-1

44-PIN PLASTIC SOP (15.24 mm (600))

detail of lead end
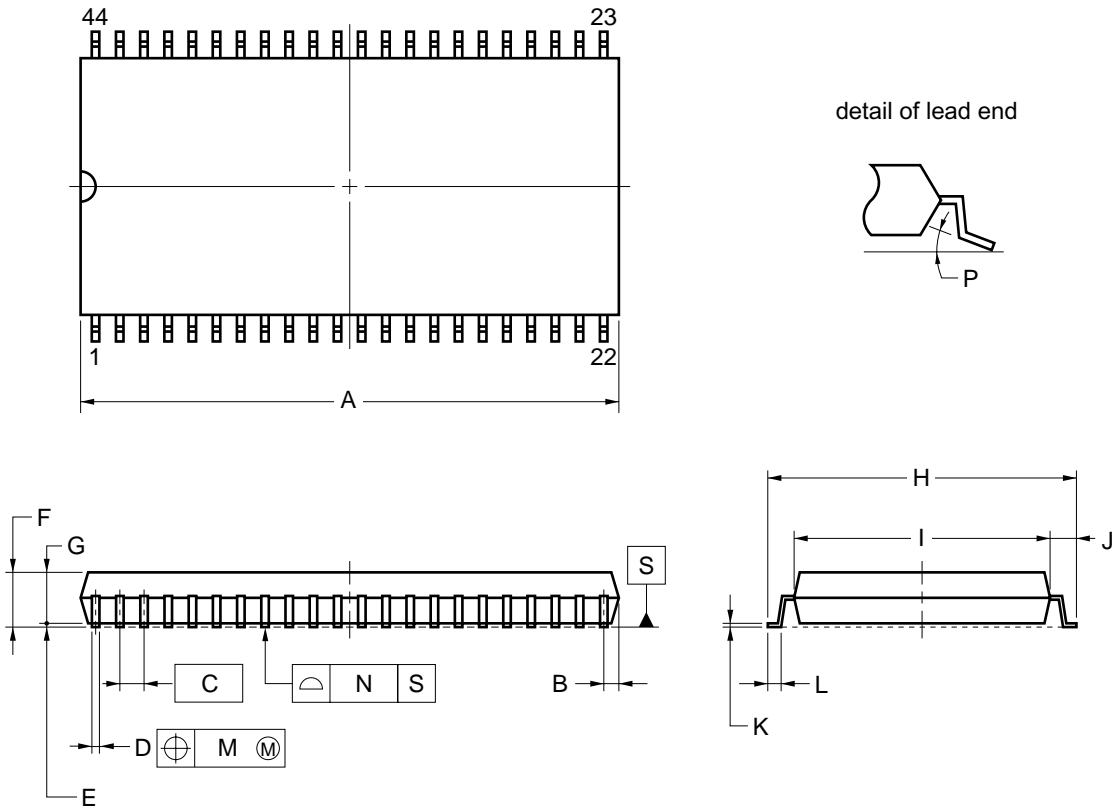
NOTE

Each lead centerline is located within 0.12 mm of
its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	$27.83^{+0.4}_{-0.05}$
B	0.78 MAX.
C	1.27 (T.P.)
D	$0.42^{+0.08}_{-0.07}$
E	0.15±0.1
F	3.0 MAX.
G	2.7±0.05
H	16.04±0.3
I	13.24±0.1
J	1.4±0.2
K	$0.22^{+0.08}_{-0.07}$
L	0.8±0.2
M	0.12
N	0.10
P	$3°^{+7°}_{-3°}$

P44GX-50-600A-4

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μPD23C64040JL, 23C64080JL.

Types of Surface Mount Device

μPD23C64040JLGY-xxx-MJH : 48-pin PLASTIC TSOP (I) (12×18) (Normal bent)
μPD23C64040JLGY-xxx-MKH : 48-pin PLASTIC TSOP (I) (12×18) (Reverse bent)
μPD23C64040JLGX-xxx : 44-pin PLASTIC SOP (15.24 mm (600))
μPD23C64080JLGY-xxx-MJH : 48-pin PLASTIC TSOP (I) (12×18) (Normal bent)
μPD23C64080JLGY-xxx-MKH : 48-pin PLASTIC TSOP (I) (12×18) (Reverse bent)
μPD23C64080JLGX-xxx : 44-pin PLASTIC SOP (15.24 mm (600))

Revision History

Edition/	Page		Type of	Location	Description
Date	This edition	Previous edition	revision		(Previous edition $\rightarrow$ This edition)
3rd edition/ Feb. 2003	p.10	p.10	Addition	AC Characteristics	Address skew time (t_{SKEW}) Note
	p.11	–	Addition		Cautions on power application
	p.12	p.11	Modification		Read Cycle Timing Chart 1

[MEMO]

[MEMO]

[MEMO]

─────────────── **NOTES FOR CMOS DEVICES** ───────────────

① **PRECAUTION AGAINST ESD FOR SEMICONDUCTORS**

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② **HANDLING OF THE APPLIED WAVEFORM OF INPUT PINS AND THE UNUSED INPUT PINS FOR CMOS**

Note:

Input levels of CMOS devices must be fixed. CMOS devices behave differently than Bipolar or NMOS devices. If the input of a CMOS device stays in an area that is between V_{IL} (MAX.) and V_{IH} (MIN.) due to the effects of noise or some other irregularity, malfunction may result. Therefore, not only the input waveform is fixed, but also the waveform changes, it is important to use the CMOS device under AC test conditions. For unused input pins in particular, CMOS devices should not be operated in a state where nothing is connected, so input levels of CMOS devices must be fixed to high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ **STATUS BEFORE INITIALIZATION OF MOS DEVICES**

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.